Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020M-6 (SOT1220-2) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- · Exposed drain pad for excellent thermal conduction

3. Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- · Computing power management

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-15	Α
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -10.5 \text{ A}; T_j = 25 \text{ °C}$		-	9.5	11.5	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



20 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	D	drain		D
3	G	gate	7	
4	S	source	2 5	$_{G}$ $($
5	D	drain	3 8 4	
6	D	drain	Transparent top view	S
7	D	drain	DFN2020M-6 (SOT1220-2)	017aaa094
8	S	source	1	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMPB09R5TP		plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1220-2		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB09R5TP	ZL

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-15	А
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-10.5	А
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-6.6	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-42	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T _{amb} = 25 °C	[1]	-	1.9	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	diode					•
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.8	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

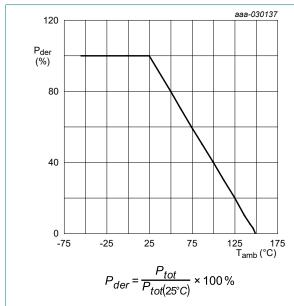


Fig. 1. Normalized total power dissipation as a function of ambient temperature

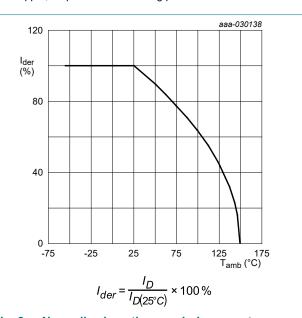


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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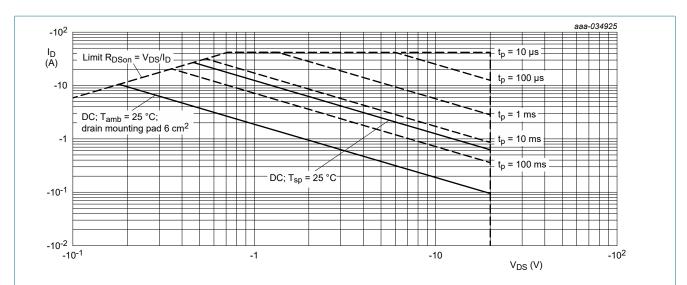


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

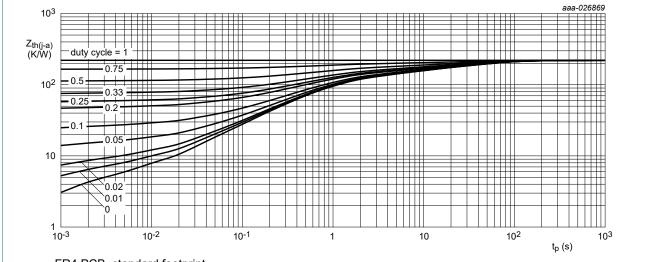
20 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

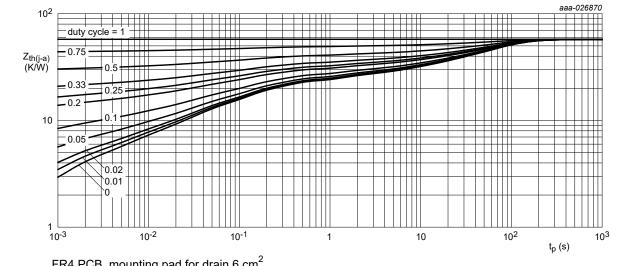
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance fi junction to ambient	thermal resistance from	in free air [[1]	-	223	256	K/W
	junction to ambient		[2]	-	57	66	K/W
		in free air, t ≤ 5 s	[2]	-	29	33	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	6	10	K/W

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



FR4 PCB, mounting pad for drain 6 cm²

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$	-0.5	-0.75	-1	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -10.5 \text{ A}; T_j = 25 \text{ °C}$	-	9.5	11.5	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -10.5 A; T _j = 150 °C	-	14	17	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -6 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	13	17	mΩ
		V_{GS} = -1.8 V; I_D = -0.5 A; T_j = 25 °C	-	21	33	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -10.5 \text{ A}; T_j = 25 \text{ °C}$	-	35	-	S
R _G	gate resistance	f = 1 MHz	-	17	-	Ω
Dynamic ch	aracteristics		·	•		
Q _{G(tot)}	total gate charge	V _{DS} = -10 V; I _D = -10.5 A; V _{GS} = -4.5 V;	-	19.5	29	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.7	-	nC
Q_{GD}	gate-drain charge		-	5.2	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}$; f = 1 MHz; $V_{GS} = 0 \text{ V}$;	-	1730	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	276	-	pF
C _{rss}	reverse transfer capacitance		-	232	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -10 V; I _D = -10.5 A; V _{GS} = -4.5 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	13	-	ns
t _{d(off)}	turn-off delay time		-	131	-	ns
t _f	fall time]	-	80	-	ns
Source-drai	in diode		'			
V_{SD}	source-drain voltage	I _S = -1.8 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

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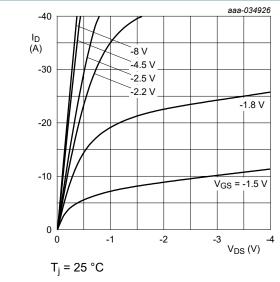


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

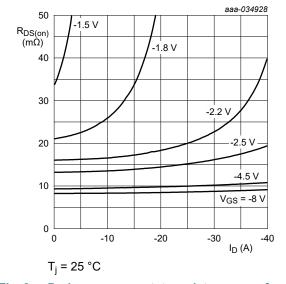


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

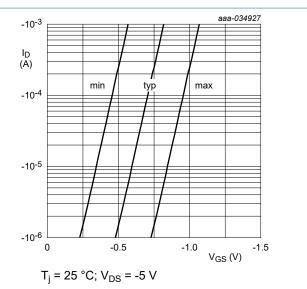


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

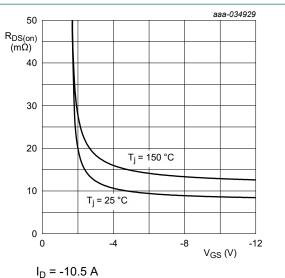


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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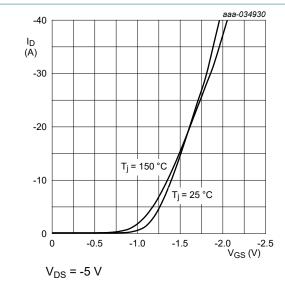


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

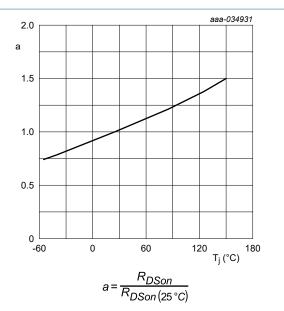


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

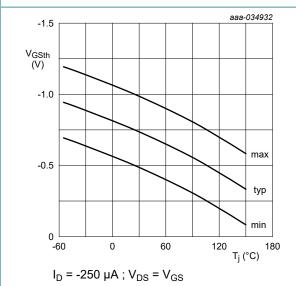


Fig. 12. Gate-source threshold voltage as a function of junction temperature

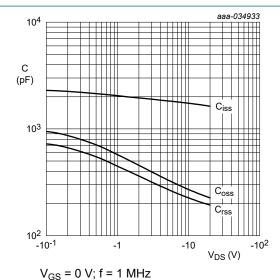


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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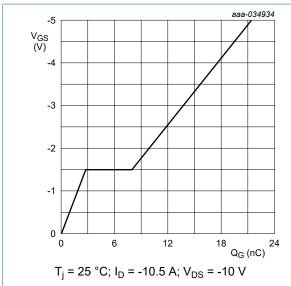


Fig. 14. Gate-source voltage as a function of gate charge; typical values

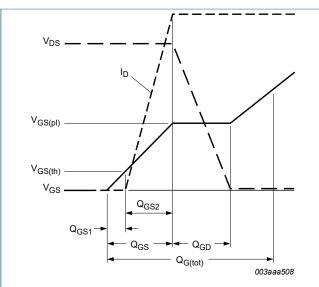


Fig. 15. Gate charge waveform definitions

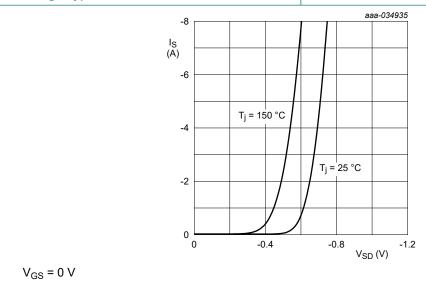
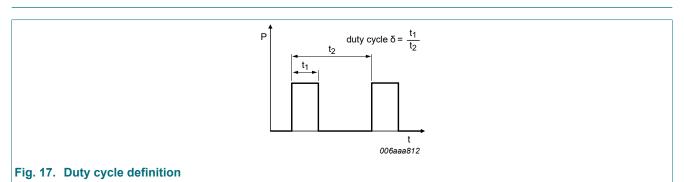


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information



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12. Package outline

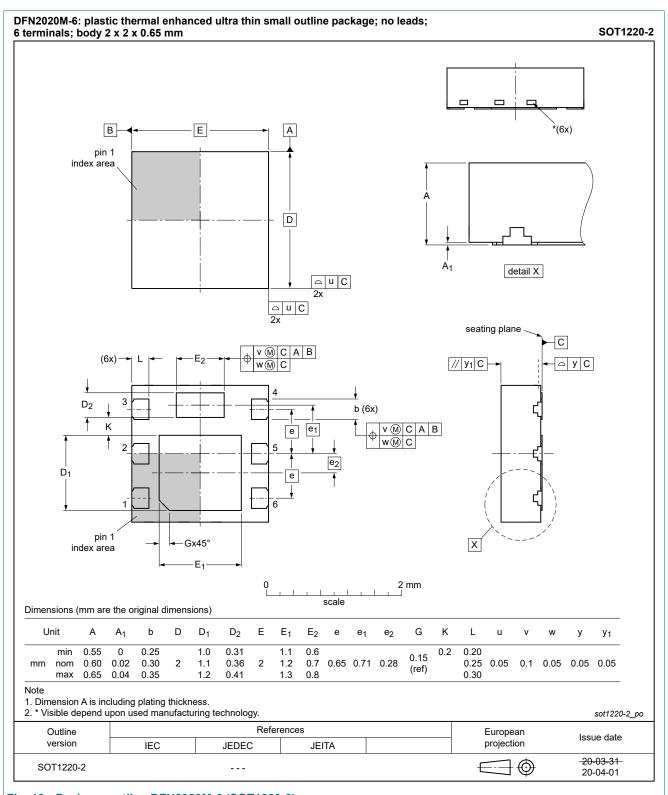
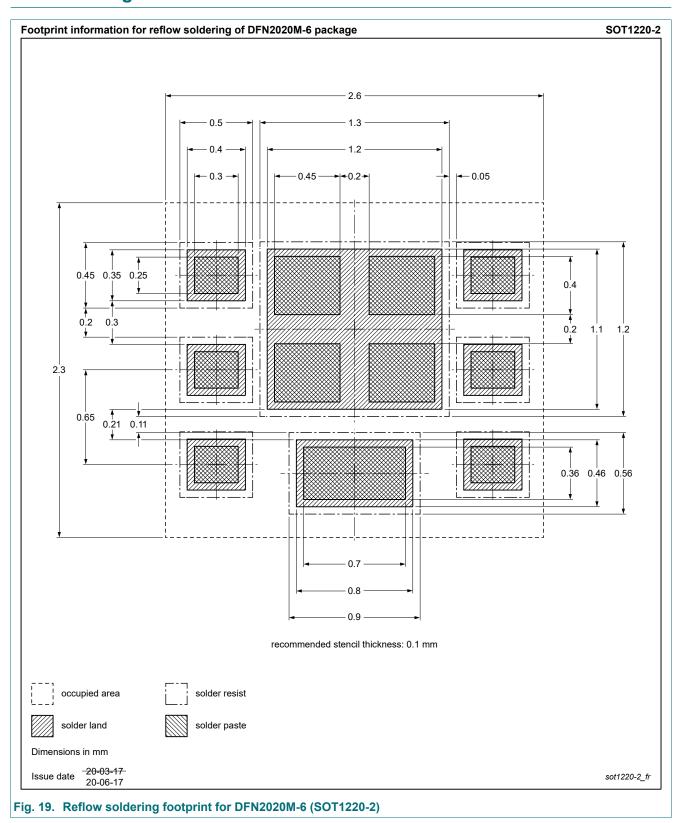


Fig. 18. Package outline DFN2020M-6 (SOT1220-2)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB09R5TP v.1	20220428	Product data sheet	-	-

20 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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